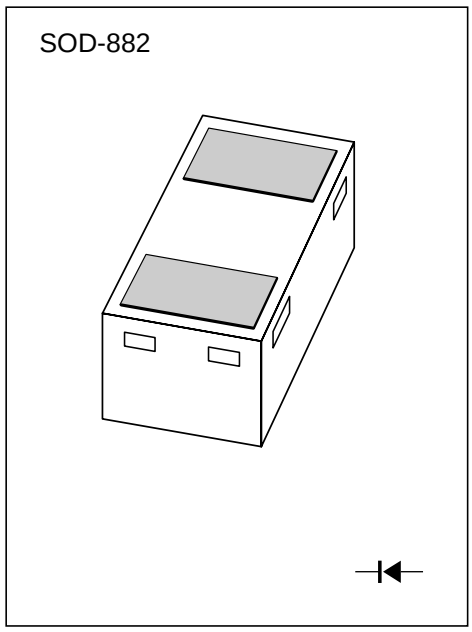
BAS16L

DESCRIPTION

The BAS16L is a high-speed switching diode fabricated in planar technology and encapsulated in a SOD882 leadless ultra small plastic package.



FEATURES

- High switching speed: max. 4 ns
- Continuous reverse voltage: max. 75 V
- Repetitive peak reverse voltage: max. 100 V
- Repetitive peak forward current: max. 500 mA
- Leadless ultra small plastic package (1 mm × 0.6 mm × 0.5 mm)
- Board space 1.17 mm^2 (approx. 10% of SOT23)
- Power dissipation comparable to SOT23.

APPLICATIONS

- General purpose switching in surface mounted circuits
- Mobile communication, digital (still) cameras, PDA and PCMCIA cards.

Marking code: S2.

LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{RRM}	repetitive peak reverse voltage		–	100	V
V_R	continuous reverse voltage		–	75	V
I_F	continuous forward current	see Fig.2; note 1	–	215	mA
I_{FRM}	repetitive peak forward current		–	500	mA
I_{FSM}	non-repetitive peak forward current	square wave; T_j = 25 °C prior to surge; see Fig.4			
		t = 1 µs	–	4	A
		t = 1 ms	–	1	A
		t = 1 s	–	0.5	A
P_{tot}	total power dissipation	T_{amb} = 25 °C; note 1	–	250	mW
T_{stg}	storage temperature		–65	+150	°C
T_j	junction temperature		–	150	°C

Note

1. Refer to SOD882 standard mounting conditions (footprint), FR4 printed-circuit board with 60 µm copper strip line.

Add: Nancheng Road,Zhangmutou Town,Dongguan City,China
Tel: 0769-82021596 E-mail:xinglin0769@163.com
Http:www.xinglindz.com

ELECTRICAL CHARACTERISTICS

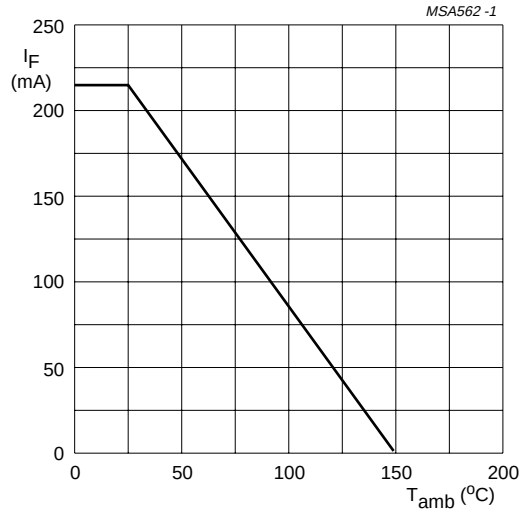
T_{amb} = 25 °C unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MAX.	UNIT
V_F	forward voltage	see Fig.3		
		I_F = 1 mA	715	mV
		I_F = 10 mA	855	mV
		I_F = 50 mA	1	V
		I_F = 150 mA	1.25	V
I_R	reverse current	see Fig.5		
		V_R = 25 V	30	nA
		V_R = 75 V	1	µA
		V_R = 25 V; T_j = 150 °C	30	µA
		V_R = 75 V; T_j = 150 °C	50	µA
C_d	diode capacitance	V_R = 0 V; f = 1 MHz; see Fig.6	1.5	pF
t_{rr}	reverse recovery time	when switched from I_F = 10 mA to I_R = 10 mA; R_L = 100 Ω; measured at I_R = 1 mA;	4	ns
V_{fr}	forward recovery voltage	when switched from I_F = 10 mA; t_r = 20 ns	1.75	V

THERMAL CHARACTERISTICS

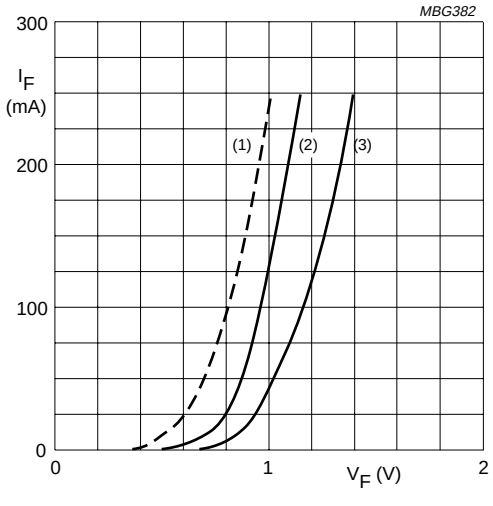
SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th\ j\text{-}a}$	thermal resistance from junction to ambient	note 1	500	K/W

GRAPHICAL DATA



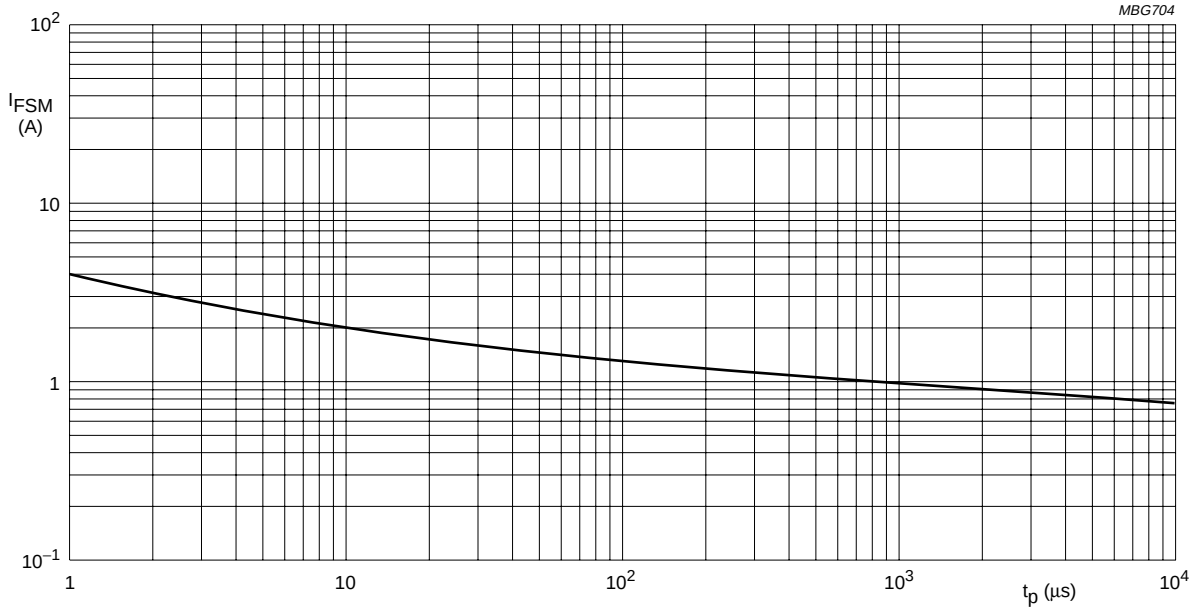
Device mounted on an FR4 printed-circuit board.

Fig.2 Maximum permissible continuous forward current as a function of ambient



(1) T_j = 150 °C; typical values.
(2) T_j = 25 °C; typical values.
(3) T_j = 25 °C; maximum value.

Fig.3 Forward current as a function of forward



Based on square wave currents.
T_j = 25 °C prior to surge.

Fig.4 Maximum permissible non-repetitive peak forward current as a function of pulse duration.

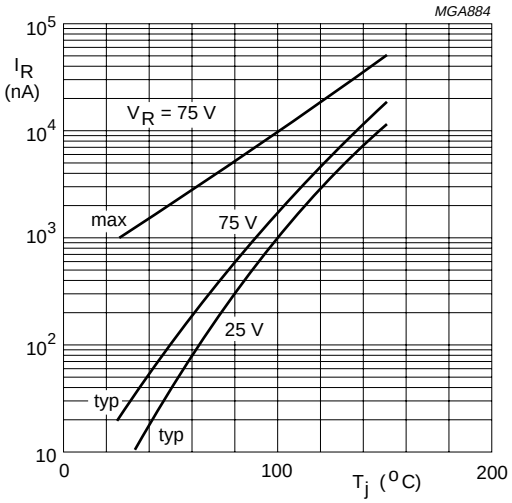
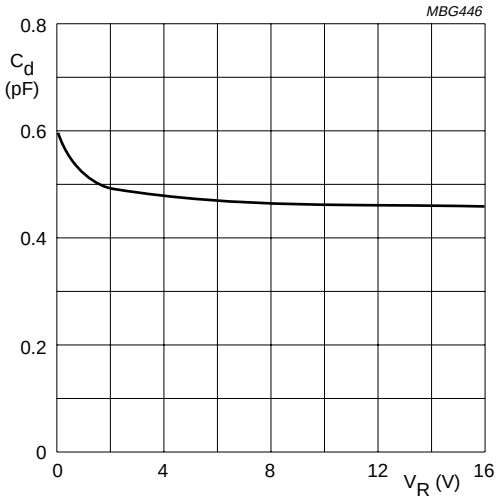


Fig.5 Reverse current as a function of junction temperature.



f = 1 MHz; T_j = 25 °C.

Fig.6 Diode capacitance as a function of reverse voltage; typical values.

Add: Nancheng Road,Zhangmutou Town,Dongguan City,China
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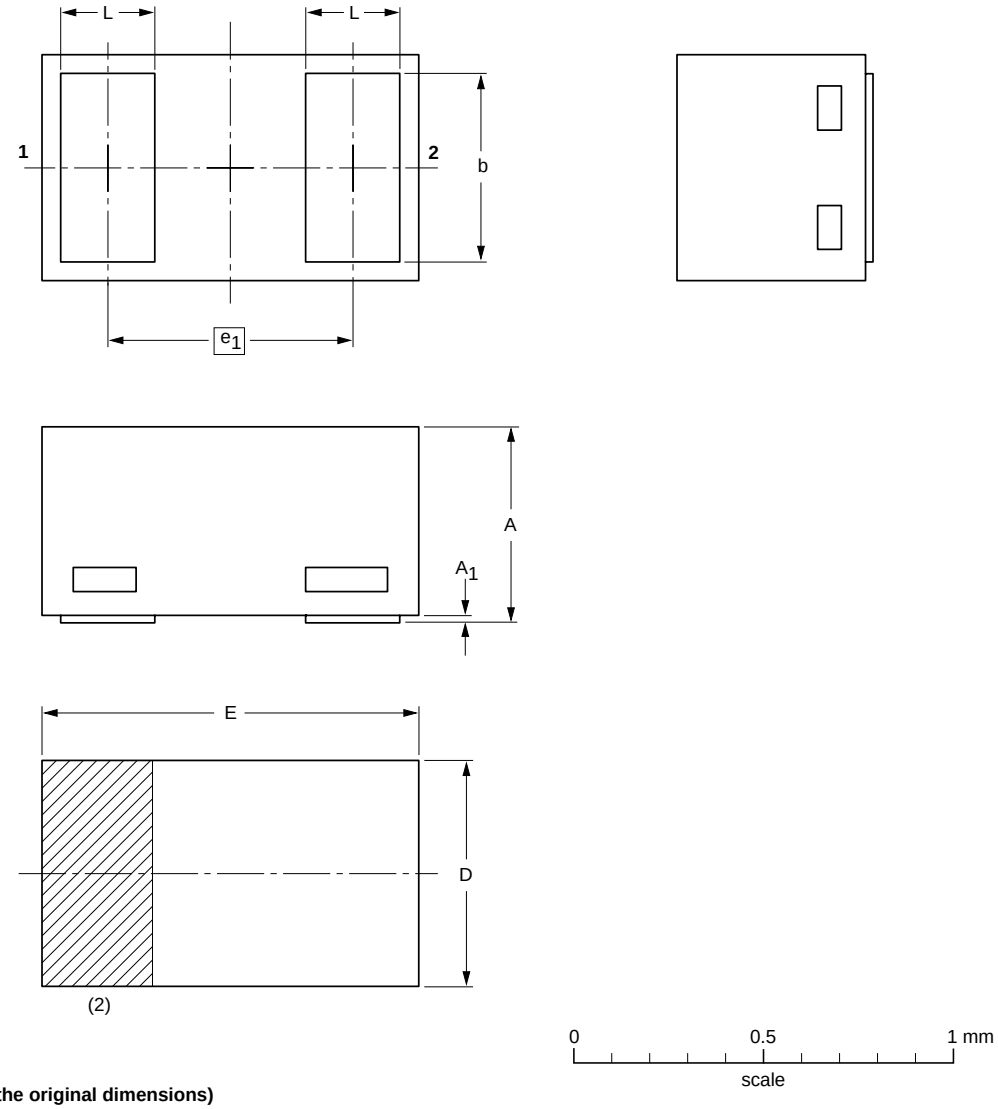
Http:www.xinglindz.com

PACKAGE OUTLINE

Leadless ultra small plastic package; 2 terminals; body 1.0 x 0.6 x 0.5 mm **SOD882**



DIMENSIONS (mm are the original dimensions)

UNIT	A(1)	A_1 max.	b	D	E	e_1	L
mm	0.50 0.46	0.03	0.55 0.47	0.62 0.55	1.02 0.95	0.65	0.30 0.22

Notes

1. Including plating thickness
2. The marking bar indicates the cathode

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA			
SOD882						~~03-04-16~~ 03-04-17

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